L Number	Hits	Search Text	I DB	Time stamp
L Number	1	("4954744").PN.	USPAT;	2003/11/07 11:06
		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	US-PGPUB	2003/11/0/ 11:06
-	1.0	coating)) with (metal adj oxide adj	USPAT; US-PGPUB	2002/11/07 10:58
-	3	particle) ((insulating insulation) adj (layer film coating)) with (metal adj oxide adj	USPAT; US-PGPUB	2002/11/07 10:57
_	0	particle) and MIM ((insulating insulation) adj (layer film coating)) with (sno2 adj particle) and	USPAT; US-PGPUB	2002/11/07 10:59
	2364	substrate substrate and (((insultating dielectric (metal adj oxide)) adj (layer film	USPAT; US-PGPUB	2002/11/07 11:04
-	131615	coating)) same particle) (insulating dielectric (metal adj oxide))	USPAT;	2002/11/07 11:06
~	2331	adj (layer film coating) (substrate and (((insultating dielectric (metal adj oxide)) adj (layer film	US-PGPUB USPAT; US-PGPUB	2002/11/07 11:08
~	3	coating)) same particle)) and substrate (((insulating dielectric (metal adj oxide)) adj (layer film coating)) with ((metal adj oxide adj particle) ((SnO2) adj	USPAT; US-PGPUB	2002/11/07 11:09
-	5	<pre>particle))) and substrate ((insulating dielectric (metal adj oxide)) adj (layer film coating)) with ((metal adj oxide adj particle) ((SnO2) adj particle))</pre>	USPAT; US-PGPUB	2002/11/07 11:18
-	0	particle) (electron adj emitting adj device) .ti. and (metal adj oxide adj particle)	USPAT;	2002/11/07 11:19
-	0	(electron adj emitting).ti. and (metal adj oxide adj particle)	USPAT; US-PGPUB	2002/11/07 11:19
-	23	(anode adj segments) and register and voltage and display	USPAT; US-PGPUB	2002/11/07 12:28
-	3	"6124676"	USPAT; US-PGPUB	2002/11/07 15:06
-	14	("3892998" "4088925" "4575721" "4650434" "5030888" "5045846" "5066890" "5075597" "5086257" "5237315" "5519520" "5674553" "5834891" "5867135").PN.	USPAT	2002/11/07 14:22
_	14	("3892998" "4088925" "4575721" "4650434" "5030888" "5045846" "5066890" "5075597" "5086257" "5237315" "5519520" "5674553" "5834891" "5867135").PN.	USPAT	2002/11/07 14:23
-	С	(vinyl adj ink) with (uv adj curable adj ink)	USPAT; US-PGPUB	2002/11/07 15:07
_	0	(vinyl adj ink) with (uv adj curable adj ink)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:08
_	0	(vinyl adj ink) same (uv adj curable adj ink)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:08
_	2	(vinyl adj ink) and (uv adj curable adj ink)	USPAT; US-PGPUB; EPO; JPO;	2002/11/07 15:10
-	0	(vinyl adj ink) with (uv adj curable)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:10
_	0	(vinyl adj ink) with (uv adj cur)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:10
-	5	(vinyl adj ink) and (uv adj curable)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/07 15:19
		(7/02 2 27 14 PM Press 1		

-	0	(electronic adj grade adj vinyl adj ink) with UV	USPAT; US-PGPUB; EPO; JPO;	2002/11/07 15:20
_	6	(electronic adj grade adj vinyl adj ink)	DERWENT USPAT; US-PGPUB;	2002/11/07 15:26
-	379	uv adj curable adj ink	EPO; JPO; DERWENT USPAT;	2002/11/07 15:26
			US-PGPUB; EPO; JPO; DERWENT	
-	170	uv adj curable adj ink (electron adj emitting adj device) and (siO2 adj layer) and (particle adj size)	USPAT; USPAT; US-PGPUB; EPO; JPO;	2002/11/07 15:27 2002/11/19 11:16
-	53	(clectron adj emitting adj device) and (particle adj size) and nm	DERWENT USPAT; US-PGPUB; EPO; JPO;	2002/11/19 11:30
	19	(electron adj emitting adj device) and substrate and ((Sio2 (silicon adj dioxide)) adj (layer coating film))	DERWENT USPAT; US-PGPUB; EPO; JPO;	2002/11/19 11:42
-	56	(substrate with sodium) and (metal adjoxide adj layer)	DERWENT USPAT; US-PGPUB	2002/11/19 11:48
-	55	"4954744"	USPAT; US-PGPUB	2002/11/19 12:15
_	2	substrate and (sodium adj blocking adj layer)	USPAT; US-PGPUB; EPO; JPO;	2002/11/19 12:18
-	4	substrate and (antistatic adj layer) and (electron adj emitting)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2002/11/19 13:55
-	0	conventinal adj pixel adj shaped adj pattern	USPAT; US-PGPUB; EPO; JPO;	2002/11/19 13:56
_	1	pixol adj shaped adj pattern	DERWENT USPAT; US-PGPUB; EPO; JPO;	2002/11/19 13:56
_	10	"5532544"	DERWENT USPAT; US-PGPUB	2002/11/22 16:28
_	1.	("4954744").PN.	USPAT; US-PGPUB	2002/11/22 16:31
-	3	(antistatic adj layer) with (silicon adj dioxide)	USPAT	2002/11/22 16:34
-	0	(antistatic adj layer) Near (silicon adj dioxide)	USPAT	2002/11/22 16:32
-	3	(antistatic adj layer) with (silicon adj dioxide, SiO)	USPAT	2002/11/22 16:35
-	10	(antistatic adj layer) with (silicon adj dioxide, SiO, MgO)	USPAT	2002/11/22 17:39
-	95 2	(electron adj emitting adj device).ti. (electron adj (emission emissive))and substrate and (metal adj oxide adj particle) and sodium and diffusion	USPAT USPAT; US-PGPUB; EPO; JPO;	2002/11/22 17:40 2003/11/07 11:10
_	2	(electron adj (emission emissive))and substrate and (metal adj oxide adj particle)	DERWENT USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 11:10
_	1444	(electron adj (emission emissive))and substrate and (particle)	USPAT; US-PGPUB; EPO; JPO; DERWENT	2003/11/07 11:11

	7	(electron adj (emission emissive))and	USPAT;	2003/11/07 11:12
		(metal adj oxide adj particle)	US-PGPUB;	
			EPO; JPO;	
			DERWENT	2000/11/05/10 05
_	339	(surface adj conduction) and (electron adj	USPAT;	2003/11/07 12:25
		emission) and particle	US-PGPUB;	
1			EPO; JPO;	
1	134658	 substrate with (((insulating dielectric)	USPAT;	2003/11/07 12:27
-	134636	layer) and (metal oxide adj particle))	US-PGPUB;	2003/11/0/12:2:
		layer, and (metal oxide adj particle)	EPO; JPO;	
			DERWENT	
_	31	substrate with (((insulating dielectric)	USPAT;	2003/11/07 12:32
1		layer)and (metal adj oxide adj particle))	US-PGPUB;	
			EPO; JPO;	
			DERWENT	
-	682	substrate with (((insulating dielectric)	USPAT;	2003/11/07 12:37
		layer)and (metal Near3 particle))	US-PGPUB;	
			EPO; JPO; DERWENT	
	229	(313/309-310, 313/351, 313/336,	USPAT:	2003/11/07 12:42
-	229	313/495-496).ccls. and metal and particle	US-PGPUB;	2005/11/0/ 12:42
		and substrate and ((insulating dielectric)	EPO; JPO;	1
		adj layer)	DERWENT	
_	2.4	((315/169.1,169)(345/74)).ccls.and	USPAT;	2003/11/07 12:44
		particle and substrate and ((insulating	US-PGPUB	
		dielectric) adj layer)		